

ABSTRACT

A semiconductor device manufacturing method includes: performing, in a non-bonded region of a combined substrate which includes a first substrate having a laser absorption layer and a first bonding layer and a second substrate having a second bonding layer and in which the first bonding layer and the second bonding layer are bonded to each other, bevel fill by injecting a filler up to a predetermined second outer peripheral position which is determined based on a first outer peripheral position in the first bonding layer; radiating laser to the laser absorption layer; and separating the first substrate from the second substrate in the combined substrate.